

ABSTRACT OF THE DISCLOSURE

Disclosed is a technique capable of improving a yield of a semiconductor device by measuring a plurality of TEGs arranged in a scribe region. A first electrode pad connected to each terminal of a TEG is formed as a rectangular, minute, isolated pattern having a side length of about 0.5 μm or shorter and constituted of an uppermost layer wiring on a semiconductor substrate, and therefore, a great number of TEGs can be laid in a first scribe region. The characteristic evaluation or the failure analysis is performed by contacting a nanoprobe having a tip radius of curvature of 0.05 μm to 0.8 μm to the first electrode pad.